

U.S. Application No. 10/502,117
Reply to Office Action of October 7, 2008
Amendment dated: February 9, 2009

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AMENDMENTS TO THE CLAIMS:

This listing of claims shall replace all prior versions, and listings, of claims in the application:

Claims 1-20. (Cancelled).

21. (Currently Amended) The high-frequency module according to claim 28 +, wherein said first organic substrate ~~insulative layer~~ is formed from either liquid crystal polymer or liquid crystal polymer having a ceramic powder dispersed therein.
22. (Currently Amended) The high-frequency module according to claim 28 +, wherein said first organic substrate ~~insulative layer~~ is formed from either benzocyclobutene or benzocyclobutene having a ceramic powder dispersed therein.
23. (Currently Amended) The high-frequency module according to claim 28 +, wherein said first organic substrate ~~insulative layer~~ is formed from either polynorbornen or polynorbornen having a ceramic powder dispersed therein.
24. (Currently Amended) The high-frequency module according to claim 28 +, wherein said first organic substrate ~~insulative layer~~ is formed from either polyphenylether or polyphenylether having a ceramic powder dispersed therein.
25. (Currently Amended) The high-frequency module according to claim 28 +, wherein said first organic substrate ~~insulative layer~~ is formed from either

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polytetrafluoroethylene or polytetrafluoroethylene having a ceramic powder dispersed therein.

26. (Currently Amended) The high-frequency module according to claim 28 ~~1~~, wherein said first organic substrate ~~insulative layer~~ is formed from either bismaleimide-triazine or bismaleimide-triazine having a ceramic powder dispersed therein.

27. (Currently Amended) The high-frequency module according to claim 28 ~~1~~, wherein said first organic substrate ~~insulative layer~~ is formed from polyimide having a ceramic powder dispersed therein.

Please add the following new claims:

28. (New). A high-frequency module comprising:
a first organic substrate having no glass fibers with conductive portions formed on top and bottom surfaces of the first organic substrate;
a second organic substrate having conductive portions formed on top and bottom surfaces of the second organic substrate;
a prepreg layer having no glass fibers exclusively located between the first and second organic substrates;
an insulating layer formed over the conductive portions formed at the top surface of the first organic substrate and wherein high frequency circuit components are formed over the insulating layer and there is no conductive portion on either the top or bottom

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surfaces of the first organic substrate located perpendicularly below high frequency circuit components that are formed over the insulating layer;

a high frequency integrated circuit located above the high frequency components and wherein conductors transmit electrical signals through the first and second organic substrates and the prepreg layer to conductive pads located beneath the second organic substrate.

29. (New). The high frequency module of claim 28, wherein the second organic substrate has glass fibers located therein.

30. (New). The high frequency module of claim 28, wherein the second organic substrate has no glass fibers located therein.

31. (New). A method of manufacturing a high-frequency module comprising:
providing a first organic substrate having no glass fibers with conductive portions formed on top and bottom surfaces of the first organic substrate;
providing a second organic substrate having conductive portions formed on top and bottom surfaces of the second organic substrate;

forming a prepreg layer having no glass fibers exclusively located between the first and second organic substrates having the conductive portions formed thereon;

forming an insulating layer over the conductive portions formed at the top surface of the first organic substrate and forming high frequency circuit components over the insulating layer and wherein there is no conductive portion on either the top or bottom surfaces of the first organic substrate located perpendicularly below high frequency circuit components that are formed over the insulating layer;

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providing a high frequency integrated circuit above the high frequency components and wherein conductors transmit electrical signals through the first and second organic substrates and the prepreg layer to conductive pads located beneath the second organic substrate.